

Chern Number and Topological Insulators - an Introduction

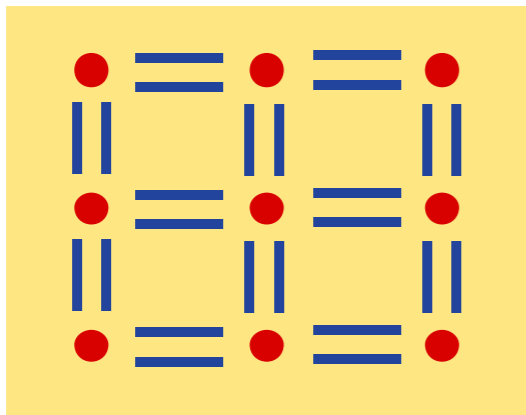
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Insulators

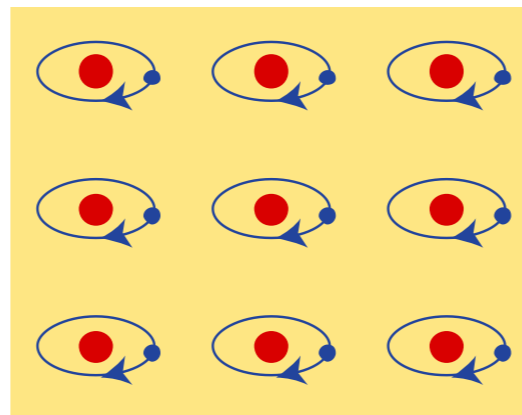
Covalent Insulator

e.g. intrinsic semiconductor

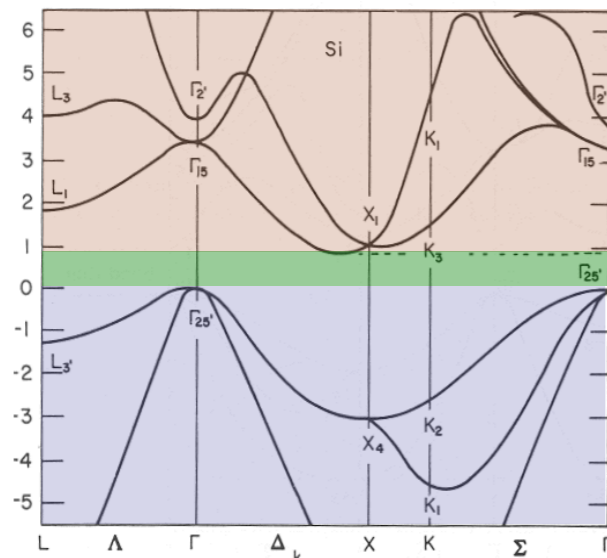


Atomic Insulator

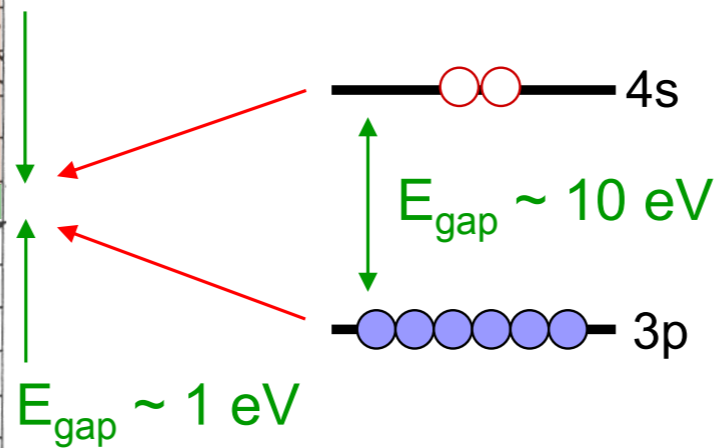
e.g. solid Ar



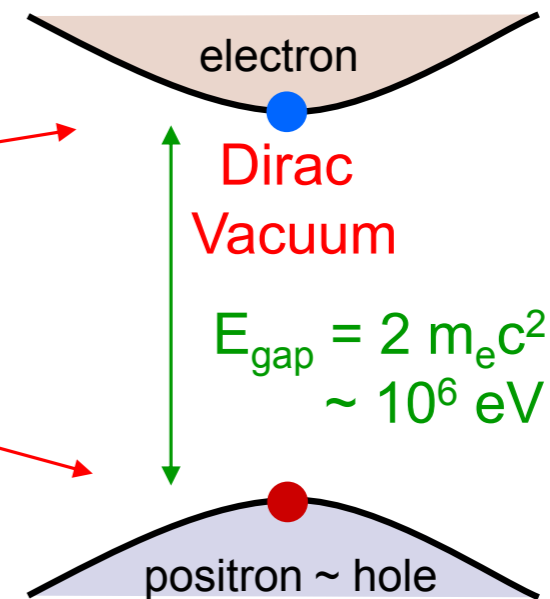
The vacuum



Silicon



$E_{\text{gap}} \sim 1 \text{ eV}$



Edge states in Dirac equation

- 2D 2-spinor Dirac equation
- Create edge by modifying parameters
- Confine electrons to edge via $m(x,y)$
- Keep translation invariance along x

$$H_D \Psi = [\sigma_x p_x + \sigma_y p_y + m \sigma_z] \Psi(x, y) = \varepsilon \Psi(x, y)$$

$$p_x \rightarrow q; \quad p_y \rightarrow -i\partial_y \quad \Psi_q(x, y) = e^{iqx} \Psi(y)$$

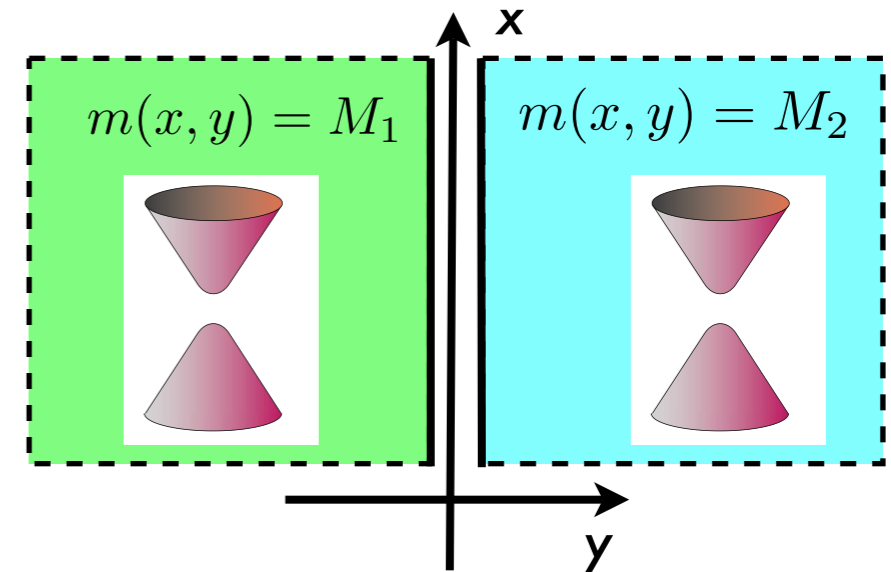
$$-i\partial_y \Psi(y) = \underbrace{[iq\sigma_z - i\sigma_x m(y) + \varepsilon\sigma_y]}_{\mathcal{A}(y)} \Psi(y)$$

- **General solution:** $\mathcal{A}(y) \quad \Psi(y) = \mathbb{Y} e^{i \int_0^y \mathcal{A} y' dy'} \Psi(0)$

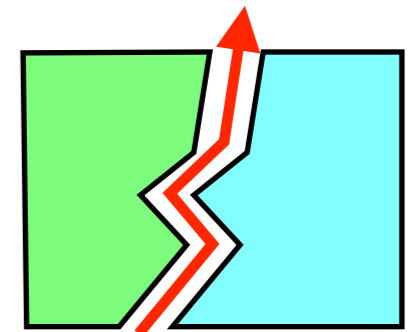
- **Ansatz:** $\varepsilon = q$ $\mathcal{A}(y) = iq \underbrace{(\sigma_z - i\sigma_y)}_{\begin{pmatrix} 1 & -1 \\ 1 & -1 \end{pmatrix}} - im(y)\sigma_x. \quad \Psi(y) = \underbrace{e^{\int_0^y m(y') dy'}}_{\begin{pmatrix} 1 \\ 1 \end{pmatrix}}$

- Unidirectional propagation (only +x)
- Robust: no scattering to bulk (gap)
no backscattering (unidirectional)
- Has to go across sample (unitarity)

- If $M_1 < 0; \quad M_2 > 0$: unidirectional (-x)



Normalizing prefactor, if
 $M_1 > 0; \quad M_2 < 0$



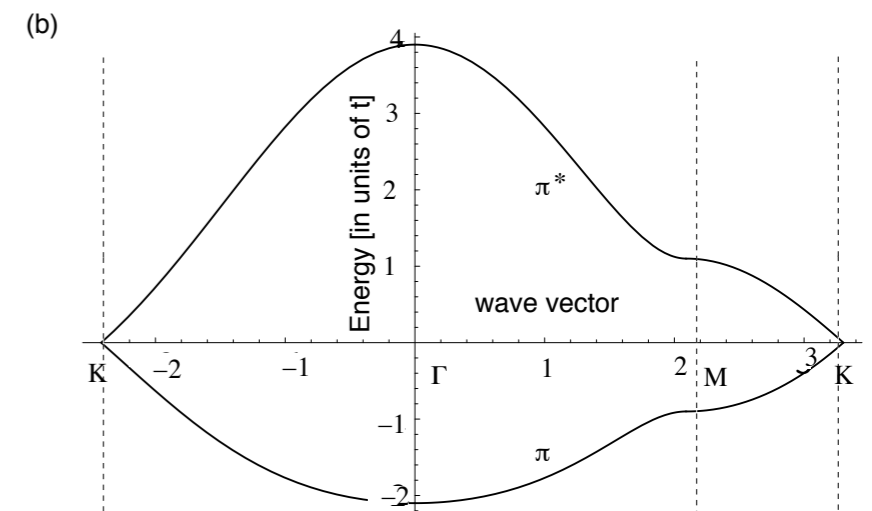
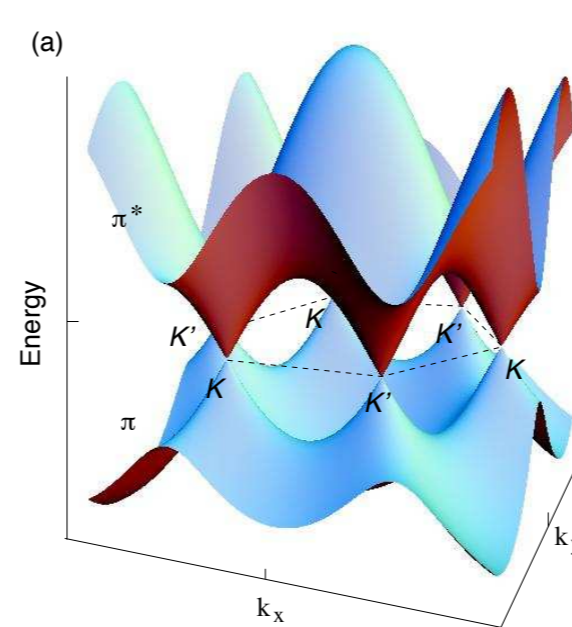
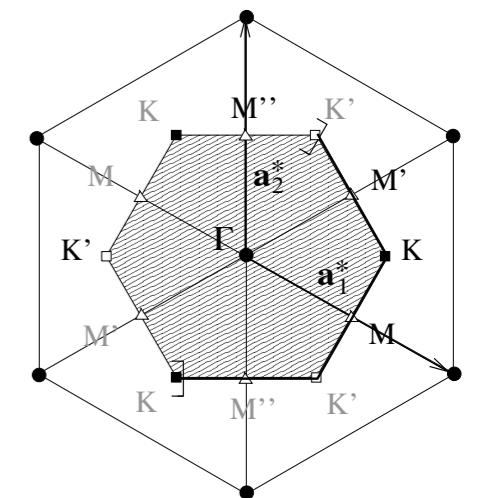
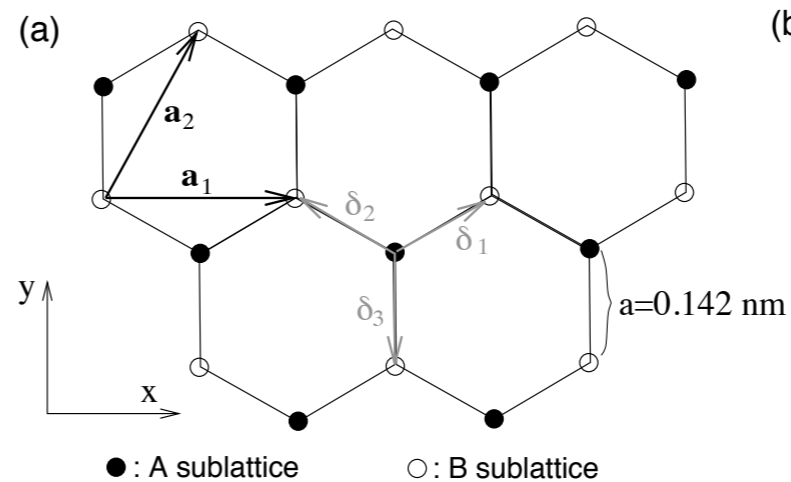
Lattice systems: several Dirac equations

- 1 electron/atom, 2 atoms/cell:
- pseudospin (sublattice)
- Gap closes at corners of Brillouin Zone ($6/3=2$ Dirac points)
- Low energy: 2 copies of massless Dirac equation \rightarrow 2 valleys, τ_z independent if no short-range scatterers

$$H = \tau_z p_x \sigma_x + p_y \sigma_y$$

- Induce mass (gap) via
 - substitution, Boron Nitride
 - electric field in bilayer graphene
- Counterpropagating edge states from opposite valleys

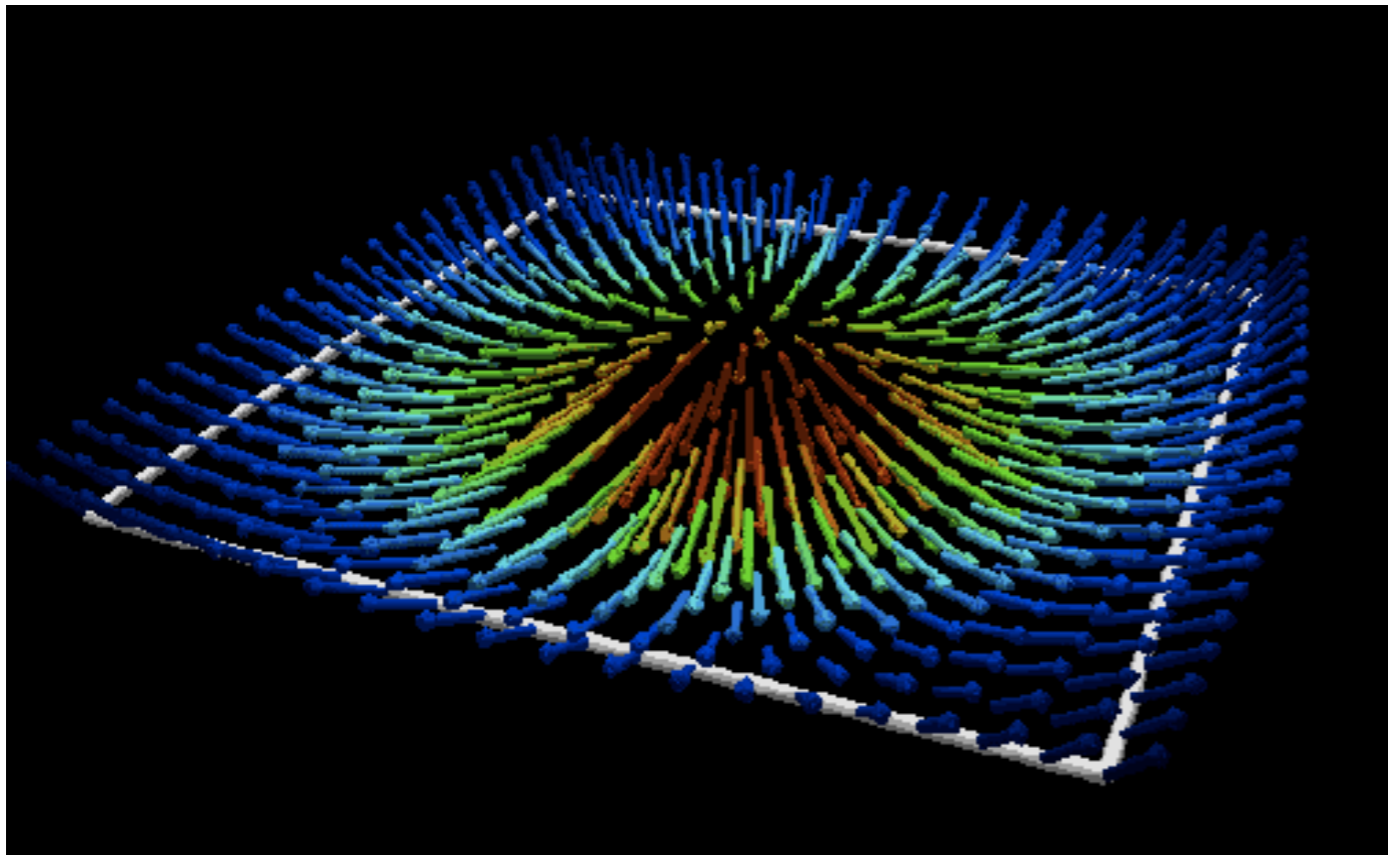
$$H = \tau_z p_x \sigma_x + p_y \sigma_y + m \sigma_z$$



Summing over valleys: Chern number

Momentum eigenstates have definite spin, 2D Brillouin zone

- Chern number: # of skyrmions in the Brillouin zone



$\mathbf{n}(\mathbf{k})$ maps from Brillouin zone (torus) to unit sphere:

- Chern number: # of times the sphere is covered by mapping

$$c_n = \frac{1}{4\pi} \int d^2 \vec{k} (\partial_{k_x} \vec{n} \times \partial_{k_y} \vec{n}) \cdot \vec{n}$$

Consider \mathbf{k} an adiabatically changed parameter:

$$A_\mu(k) = -i \langle n(k) | \frac{\partial}{\partial k_\mu} | n(k) \rangle$$

- Chern #: Integral of Berry phase around the Brillouin zone

= integral of Berry flux in the Brillouin zone

$$F_{xy}(k) = \frac{\partial A_y}{\partial k_x} - \frac{\partial A_x}{\partial k_y}$$

$$C_1 = \frac{1}{2\pi} \int dk_x dk_y F_{xy}(k)$$

efficient discretization: need only 10 or so k-points

[Fukui, Hatsugai, Suzuki, JPSJ (2005)]

Chern #: needs Time Reversal Symmetry Breaking

- Chern number always 0 if we have a global basis
- Time reversal symmetry:
 - Complex conjugation in position and preferred internal basis: $K\Psi(k) = \Psi^*(-k)$
 - k-independent internal unitary rotation:

$$\exists T \in U(N) : \forall k \in BZ : TKH(k)KT^\dagger = H(k)$$

- Antiunitary symmetry, $\Theta = TK$

- With time reversal invariance, we always have a global basis: Chern # = 0
- Break time reversal invariance via magnetic field
- Graphene, Haldane [PRL, 1988]: staggered magnetic field, simple calculation

- 0 average field \Rightarrow no need for magnetic Brillouin Zone
- Peierls substitution only for NNN hoppings
- Competition between conventional and topological gap

